

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-6. (Canceled)

7. (Currently Amended) A method of manufacturing a wiring comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width; and

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with sixth width,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

8. (Currently Amended) A method of manufacturing a wiring comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width; and

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

9. (Currently Amended) A method of manufacturing a wiring comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width;

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with sixth width; and

subjecting the third-shaped conductive layer to a plasma treatment,
wherein a cross-section of edges of at least one of the first conductive layer, the
second conductive layer, [[or]] and the third conductive layer has a taper shape.

10. (Currently Amended) A method of manufacturing a wiring comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width;

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width; and

subjecting the fourth-shaped conductive layer to a plasma treatment,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

11. (Original) A method of manufacturing a wiring according to any one of claims 7 to 10, wherein the first conductive layer comprises at least one selected from the group consisting of W and Mo.

12. (Original) A method of manufacturing a wiring according to any one of claims 7 to 10, wherein the second conductive layer comprises Al.

13. (Original) A method of manufacturing a wiring according to any one of claims 7 to 10, wherein the third conductive layer comprises Ti.

14. (Currently Amended) A method of manufacturing a wiring according to any one of claims [[7 to]] 9 and 10, wherein the plasma treatment is conducted ~~by using oxygen or a gas mainly containing oxygen, or H₂O in an atmosphere containing at least one of oxygen and H₂O.~~

15.-20. (Canceled)

21. (Currently Amended) A method of manufacturing a wiring board comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of a first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width; and

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with the sixth width,

wherein a cross-section of edges of at least one of the first conductive layer with the fourth width, the second conductive layer with the fifth width, [[or]] and the third conductive layer with the sixth width has a taper shape.

22. (Currently Amended) A method of manufacturing a wiring board comprising the steps of:

forming a first-shaped conductive layer composed of a stack of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width; and

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width,

wherein a cross-section of edges of at least one of the first conductive layer with the fourth width, the second conductive layer with the fifth width, [[or]] and the third conductive layer with the sixth width has a taper shape.

23. (Currently Amended) A method of manufacturing a wiring board comprising the steps of:

forming a first conductive layer on an insulating surface;

forming a second conductive layer on the first conductive layer;

forming a third conductive layer on the second conductive layer;
~~etching patterning the first to first, second and~~ third conductive layers by dry etching method to form a conductive layer with a taper portion; and
subjecting the conductive layer with a taper portion to a plasma treatment.

24. (Currently Amended) A method of manufacturing a wiring board comprising the steps of:

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of a first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width;

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with the sixth width; and

subjecting the third-shaped conductive layer to a plasma treatment,

wherein a cross-section of edges of at least one of the first conductive layer with the fourth width, the second conductive layer with the fifth width, [[or]] and the third conductive layer with the sixth width has a taper shape.

25. (Currently Amended) A method of manufacturing a wiring board comprising the steps of:

forming a first-shaped conductive layer composed of a stack of a first conductive layer, a second conductive layer, and a third conductive layer on an insulating surface;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width;

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width; and

subjecting the fourth-shaped conductive layer to a plasma treatment,

wherein a cross-section of edges of at least one of the first conductive layer with the fourth width, the second conductive layer with the fifth width, [[or]] and the third conductive layer with the sixth width has a taper shape.

26. (Original) A method of manufacturing a wiring board according to any one of claims 21 to 25, wherein the first conductive layer comprises at least one selected from the group consisting of W and Mo.

27. (Original) A method of manufacturing a wiring board according to any one of claims 21 to 25, wherein the second conductive layer comprises Al.

28. (Original) A method of manufacturing a wiring board according to any one of claims 21 to 25, wherein the third conductive layer comprises Ti.

29. (Currently Amended) A method of manufacturing a wiring board according to any one of claims [[21]] 23 to 25, wherein the plasma treatment is conducted ~~by using oxygen or a gas mainly containing oxygen, or H₂O in an atmosphere containing at least one of oxygen and H₂O.~~

30.-36. (Canceled)

37. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a substrate;

forming a gate insulating film on the semiconductor layer;

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on the gate insulating film;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width; and

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with sixth width,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

38. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a substrate;

forming a gate insulating film on the semiconductor layer;

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on the gate insulating film;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width; and

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

39. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a substrate;

forming a gate insulating film on the semiconductor layer;

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on the gate insulating film;

etching the first conductive layer, the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of

the first conductive layer with a first width, a second conductive layer with a second width, and a third conductive layer with a third width;

etching the second conductive layer with the second width and the third conductive layer with the third width to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with sixth width; and

subjecting the third-shaped conductive layer to a plasma treatment,

wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

40. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer over a substrate;

forming a gate insulating film on the semiconductor layer;

forming a first-shaped conductive layer comprising a lamination of a first conductive layer, a second conductive layer, and a third conductive layer on the gate insulating film;

etching the second conductive layer and the third conductive layer to form a second-shaped conductive layer comprising a lamination of the first conductive layer, a second conductive layer with a first width, and a third conductive layer with a second width;

etching the first conductive layer to form a third-shaped conductive layer comprising a lamination of a first conductive layer with a third width, the second conductive layer with the first width, and the third conductive layer with the second width;

etching the second conductive layer with the first width and the third conductive layer with the second width to form a fourth-shaped conductive layer comprising a

lamination of a first conductive layer with a fourth width, a second conductive layer with a fifth width, and a third conductive layer with a sixth width; and

subjecting the fourth-shaped conductive layer to a plasma treatment,
wherein a cross-section of edges of at least one of the first conductive layer, the second conductive layer, [[or]] and the third conductive layer has a taper shape.

41. (Original) A method of manufacturing a semiconductor device according to any one of claims 37 to 40, wherein the first conductive layer comprises at least one selected from the group consisting of W and Mo.

42. (Original) A method of manufacturing a semiconductor device according to any one of claims 37 to 40 , wherein the second conductive layer comprises Al.

43. (Original) A method of manufacturing a semiconductor device according to any one of claims 37 to 40 , wherein the third conductive layer comprises Ti.

44. (Currently Amended) A method of manufacturing a semiconductor device according to any one of claims [[37 to]] 39 and 40, wherein the plasma treatment is conducted by using oxygen or a gas mainly containing oxygen, or H₂O in an atmosphere containing at least one of oxygen and H₂O.

45. (Original) A method of manufacturing a semiconductor device according to any one of claims 37 to 40, wherein the semiconductor device is at least one selected from the group consisting of a liquid crystal display device and a light-emitting device.

46. (Original) A method of manufacturing a semiconductor device according to any one of claims 37 to 40, wherein the semiconductor device is at least one selected

from the group consisting of a personal computer, a player using a recording medium, and a display.

47. (New) A method of manufacturing a wiring board according to claim 23, wherein a surface of the taper portion of the conductive layer is oxidized by said plasma treatment.